30 July 200

Hits DB L Numb r Search Text USPAT; 2003/07/29 0 476526.apn. US-PGPUB: 11:13 EPO; JPO; DERWENT 2003/07/29 USPAT; 6547937.pn. US-PGPUB; 14:25 EPO; JPO; **DERWENT** 2003/07/28 152 204/\$.ccls. and (cleaning adj electrode) USPAT: 16:24 US-PGPUB; EPO; JPO; DERWENT 2003/07/28 17 (204/\$.ccls. and (cleaning adj electrode)) and USPAT; (microelectronic or wafer or semiconductor) US-PGPUB; 16:24 EPO: JPO: DERWENT 12396 204/\$.ccls. and (anode same cathode) 2003/07/29 USPAT; US-PGPUB; 10:53 EPO; JPO; DERWENT 782216.apn. USPAT: 2003/07/29 US-PGPUB; 13:12 EPO; JPO; DERWENT 59395 USPAT; 2003/07/29 204/\$.ccls. US-PGPUB; 13:12 EPO; JPO; DERWENT 35240 205/\$.ccls. 2003/07/29 USPAT; US-PGPUB; 13:13 EPO; JPO; **DERWENT** 83968 204/\$.ccls. 205/\$.ccls. USPAT: 2003/07/29 US-PGPUB; 13:13 EPO; JPO; DERWENT 2003/07/29 10782 (204/\$.ccls. 205/\$.ccls.) and (microelectronic or USPAT; semiconductor or wafer) US-PGPUB; 13:13 EPO; JPO; DERWENT 1310 ((204/\$.ccls. 205/\$.ccls.) and (microelectronic or USPAT; 2003/07/29 semiconductor or wafer)) and ((second or secondary US-PGPUB; 13:14 or another or additional) near (electrode or cathode EPO; JPO; or anode)) DERWENT 2003/07/29 574 ((204/\$.ccls. 205/\$.ccls.) and (microelectronic or USPAT; 13:18 semiconductor or wafer)) and ((clean\$5 or strip\$5 US-PGPUB; deposit) near2 (anode or cathode or electrode)) EPO; JPO;

DERWENT

	T			
-	174	(((204/\$.ccls. 205/\$.ccls.) and (micro 1 ctronic or	USPAT;	2003/07/29
		semiconductor or wafer)) and ((s cond or secondary	US-PGPUB;	13:18
		or another or additional) near (el ctrod or cathode	EPO; JPO;	
		or anode))) and (((204/\$.ccls. 205/\$.ccls.) and	DERWENT	
		(micro ctronic or semiconductor or wafer)) and		
		((clean\$5 or strip\$5 d posit) near2 (anode or		•
		cathode or electrode)))		
_	93	((((204/\$.ccls. 205/\$.ccls.) and (microelectronic or	USPAT;	2003/07/29
	, ,	semiconductor or wafer)) and ((second or secondary	US-PGPUB;	13:18
		or another or additional) near (electrode or cathode	EPO; JPO;	
		or anode))) and (((204/\$.ccls. 205/\$.ccls.) and	DERWENT	
		(microelectronic or semiconductor or wafer)) and	DERVEIN	
		((clean\$5 or strip\$5 deposit) near2 (anode or		
		cathode or electrode)))) and (etch\$5)		0000/07/00
-	462	205/640,646,648,652,686.ccls.	USPAT;	2003/07/29
		·	US-PGPUB;	14:26
	1		EPO; JPO;	·
			DERWENT	
-	98	205/640,646,648,652,686.ccls. and clean\$5	USPAT;	2003/07/29
			US-PGPUB;	15:10
		· .	EPO; JPO;	
1			DERWENT	
_	744	204/224m.ccls.	USPAT;	2003/07/29
:			US-PGPUB;	15:10
			EPO; JPO;	
			DERWENT	
_	2427	204/275.1,237,242,280.ccls.	USPAT;	2003/07/30
			US-PGPUB;	15:02
		·	EPO; JPO;	
			DERWENT	
	3092	204/224m.ccls. 204/275.1,237,242,280.ccls.	USPAT;	2003/07/29
	3072	20 1/ 22 1111.00/3. 20 1/ 2/ 0.1/20/ /2 12/200.00/3.	US-PGPUB;	15:10
1	'		EPO; JPO;	13.10
			DERWENT	
	147	(204/224m cale 204/275 1 227 242 280 cale) and	USPAT;	2003/07/29
	167	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	US-PGPUB;	15:12
		((electrochem\$7 or electrol\$7 or (electro adj		13.16
		chem\$7)) near2 (etch\$5 or polish\$3))	EPO; JPO;	
		(004/004) L. 004/0754-007-040-000	DERWENT	2002/07/20
_	100	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
	1	(electropolish\$5)	US-PGPUB;	15:12
			EPO; JPO;	
	1		DERWENT	
-	57	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
		((electropolish\$5) with (electrode or anode or	US-PGPUB;	15:13
		cathode))	EPO; JPO;	
			DERWENT	
-	87	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and	USPAT;	2003/07/29
		(((electrochem\$7 or electrol\$7 or (electro adj	US-PGPUB;	15:21
		chem\$7)) near2 (etch\$5 or polish\$3)) with	EPO; JPO;	
•		(electrode or cathode or anode))	DERWENT	
-	809	(204/\$.ccls. 205/\$.ccls.) and ((((builld or built) adj	USPAT;	2003/07/29
		up) or d posit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:23
,		cathod or electrode) with (distance or gap or	EPO; JPO;	
		spacing))	DERWENT	

	179	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
-	1/9	up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:25
		cathode or el ctrode) with (distanc or gap or	EPO; JPO;	-0.50
		spacing)) same (remov\$4 or cl an\$3 or strip\$4 or	DERWENT	
		etch\$4))		
_	804	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:28
		cathode or electrode) with (distance or gap or	EPO; JPO;	·
	•	spacing)) same ((remov\$4 or clean\$3 or strip\$4 or	DERWENT	
		etch\$4) with ((builld or built) adj up) or deposit\$5 or		
		collect\$3))		
-	133	(204/\$.ccls. 205/\$.ccls.) and (((((builld or built) adj	USPAT;	2003/07/29
·		up) or deposit\$5 or collect\$3) with (electrode or	US-PGPUB;	15:29
		cathode or electrode) with (distance or gap or	EPO; JPO;	
		spacing)) same ((remov\$4 or clean\$3 or strip\$4 or	DERWENT	
		etch\$4) with (((builld or built) adj up) or deposit\$5		
		or collect\$3)))		0000 (07 (00
	3	(("6500324") or ("6174425")).PN.	USPAT;	2003/07/30
			US-PGPUB;	09:33
			EPO; JPO;	
			DERWENT; IBM_TDB	
	9947	204/\$.ccls. and (microelectronic or semiconductor or	USPAT;	2003/07/30
-	8867	wafer)	US-PGPUB;	10:30
		water)	EPO; JPO;	10.50
			DERWENT;	
			IBM_TDB	
_	2347	(204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	10:31
		(fluid or solution or electrolyte))	EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
-	1056	(204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	13:15
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
	. =	or opening or inlet or outlet))	IBM_TDB	0002/07/00
-	__ 65	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	13:17
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO; DERWENT;	
		or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (mesh with anode)	IBM_TDB	
_	. 75	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
-	/5	or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:14
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	- ''- '
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (mesh with (anode	IBM_TDB	
		or porous))	_	
-	160	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrod) with	US-PGPUB;	14:15
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passag or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode with (m sh	IBW_TDB	
	<u> </u>	or porous))		

-	110	((204/\$.ccls. and (microel ctronic or semiconductor	USPAT;	2003/07/30
		or waf r)) and ((anod or cathode or electrod) with	US-PGPUB;	14:15
		(fluid or solution or lectrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inl t or outl t))) and (anode with	IBM_TDB	
		rotat\$5)		
-	125	((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:16
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode near2	IBM_TDB	
		(rotat\$5 or mov\$7))	_	
_	60	(((204/\$.ccls. and (microelectronic or semiconductor	USPAT;	2003/07/30
		or wafer)) and ((anode or cathode or electrode) with	US-PGPUB;	14:23
		(fluid or solution or electrolyte) with (conduit or path	EPO; JPO;	
		or pathway or port or passage or passageway or flow	DERWENT;	
		or opening or inlet or outlet))) and (anode near2	IBM_TDB	
		(rotat\$5 or mov\$7))) and (((204/\$.ccls. and		
		(microelectronic or semiconductor or wafer)) and		
	[((anode or cathode or electrode) with (fluid or		
		solution or electrolyte) with (conduit or path or		
		pathway or port or passage or passageway or flow or		
		opening or inlet or outlet))) and (anode with (mesh or		
		porous)))		
_	2	6197182.pn.	USPAT;	2003/07/30
	- 1	- 0157 102.pm _	US-PGPUB;	14:35
			EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	
_	1349	204/\$.ccls. and (solution with ((rins\$4 or clean\$5)	USPAT;	2003/07/30
	1017	and (electroplat\$5 or electroly\$6 or plating)))	US-PGPUB;	14:39
			EPO; JPO;	
		·	DERWENT;	
		·	IBM_TDB	.*
	765	(204/\$.ccls. and (solution with ((rins\$4 or clean\$5)	USPAT;	2003/07/30
	, 03	and (electroplat\$5 or electroly\$6 or plating)))) not	US-PGPUB;	14:40
		rinsed!	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM_TDB	
_	3	((("6103096") or ("5614076") or ("5531874") or	USPAT;	2003/07/30
		("5486282") or ("5543032") or ("5536388") or	US-PGPUB;	14:43
1		("5567300") or ("5284554")).PN.) and ((rins\$ or	EPO; JPO;	
		clean\$) with (plating or electroly\$5 or	DERWENT;	
		electroplat\$5))	IBM_TDB	
_	5	6103096.URPN.	USPAT	2003/07/30
			33	14:44
_	15	(("6103096") or ("5614076") or ("5531874") or	USPAT;	2003/07/30
		("5486282") or ("5543032") or ("5536388") or	US-PGPUB;	14:49
		("5567300") or ("5284554")).PN.	EPO; JPO;	•
		(000,000) 01 (020,100 +)),114.	DERWENT;	
			IBM_TDB	
1_	29	5567300.URPN.	USPAT	2003/07/30
1			33.7.1	14:47
			l	47.7/

	T	FF 42020 LIDDA	LICDAT	2002/07/20
-	20	5543032.URPN.	USPAT	2003/07/30
			LICD AT	14:48
-	6	5536388.URPN.	USPAT	2003/07/30
				14:48
-	15	5486282.URPN.	USPAT	2003/07/30
			l	14:48
-	19	5284554.URPN.	USPAT	2003/07/30
				14:48
-	62	5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
		5486282.URPN. 5284554.URPN.	US-PGPUB;	14:49
			EPO; JPO;	
-		•	DERWENT;	
			IBM_TDB	
-	0	(5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
		5486282.URPN. 5284554.URPN.) and (clean\$5 with	US-PGPUB;	14:50
		(electrode or cathode or anode))	EPO; JPO;	
			DERWENT;	
-			IBM_TDB	
-	26	(5567300.URPN. 5543032.URPN. 5536388.URPN.	USPAT;	2003/07/30
		5486282.URPN. 5284554.URPN.) and (remov\$5 with	US-PGPUB;	14:55
		(electrode or cathode or anode))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	83968	204/\$.ccls. 205/\$.ccls.	USPAT;	2003/07/30
	•		US-PGPUB;	14:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	3	(204/\$.ccls. 205/\$.ccls.) and (electrochem\$7 near	USPAT;	2003/07/30
		(micromachin\$5 or machin\$5)) and (clean\$ near	US-PGPUB;	14:57
		(electrode or cathode or anode))	EPO; JPO;	
	<u> </u>	"	DERWENT;	
			IBM_TDB	
-	295	204/275.1,237,242,280.ccls. and (titanium with	USPAT;	2003/07/30
		(platinum or platinized))	US-PGPUB;	15:05
		,	EPO; JPO;	
	·		DERWENT	
-	83	(204/275.1,237,242,280.ccls. and (titanium with	USPAT;	2003/07/30
		(platinum or platinized))) and (microelectronic or	US-PGPUB;	15:06
		semiconductor or wafer)	EPO; JPO;	
			DERWENT	
L			DCKTACIAL	l